



40V +175°C DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(on) max}	I _D T _A = +25°C
40V	15mΩ @ V _{GS} = 10V	8.6A
	$20m\Omega$ @ $V_{GS} = 4.5V$	7.5A

Features and Benefits

- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching Ensures More Reliable and Robust End Application
- Low R_{DS(ON)} Minimizes Power Losses
- Low Qg Minimizes Switching Losses
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

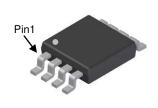
Description and Applications

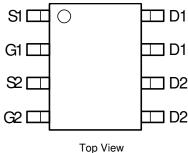
This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

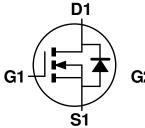
- Engine Management Systems
- Body Control
- DC-DC Converters

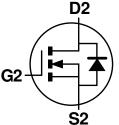
Mechanical Data

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Tin Finish Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (2)
- Weight: 0.074 grams (Approximate)









Top View
Pin Configuration

Equivalent Circuit

Ordering Information (Note 5)

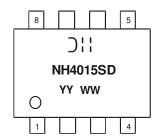
Top View

Part Number	Case	Packaging
DMNH4015SSDQ-13	SO-8	2,500/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/product_compliance_definitions.html.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



J!! = Manufacturer's Marking
NH4015SD = Product Type Marking Code
YYWW = Date Code Marking
YY = Year (ex: 16 = 2016)
WW = Week (01 - 53)



Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Units		
Drain-Source Voltage			V_{DSS}	40	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current (Note 7) V _{GS} = 10V	Steady State	$T_A = +25$ °C $T_A = +70$ °C	I _D	8.6 6.9	А
	t<10s	$T_A = +25$ °C $T_A = +70$ °C	I _D	11.0 8.8	А
Maximum Body Diode Forward Current (Note 7)			Is	2.2	Α
Pulsed Drain Current (380µs pulse, duty cycle = 1%)			I _{DM}	80	Α
Avalanche Current (Note 8) L = 0.1mH			I _{AS}	25	Α
Avalanche Energy (Note 8) L = 0.1mH			Eas	33	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units	
Total Power Dissipation (Note 6)	$T_A = +25$ °C	Pn	1.4	W
Total Fower Dissipation (Note o)	T _A = +70°C	PD	0.9	
Thermal Resistance, Junction to Ambient (Note 6)	Steady state	В	111	°C/W
Thermal nesistance, Junction to Ambient (Note 6)	t<10s	$R_{ hetaJA}$	66	
Total Bower Discinction (Note 7)	$T_A = +25^{\circ}C$	Б	2.0	w
Total Power Dissipation (Note 7)	T _A = +70°C	P_{D}	1.2	
Thermal Resistance, Junction to Ambient (Note 7)	Steady state	В	75	°C/W
Thermal nesistance, Junction to Ambient (Note 7)	t<10s	$R_{ heta JA}$	45	
Thermal Resistance, Junction to Case (Note 7)		$R_{ heta JC}$	10.4	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage	BV _{DSS}	40	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μΑ	$V_{DS} = 40V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)	ON CHARACTERISTICS (Note 9)						
Gate Threshold Voltage	V _{GS(TH)}	1	_	3	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
Static Drain-Source On-Resistance		_	10	15	mΩ	$V_{GS} = 10V, I_D = 12A$	
Static Dialii-Source Oil-nesistance	R _{DS(ON)}	_	12	20	11122	$V_{GS} = 4.5V, I_D = 10A$	
Diode Forward Voltage	V_{SD}	_	0.7	1.0	V	$V_{GS} = 0V, I_{S} = 1A$	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	C _{iss}		1,938	-		V _{DS} = 15V, V _{GS} = 0V, f = 1.0MHz	
Output Capacitance	Coss		156	-	pF		
Reverse Transfer Capacitance	C _{rss}		126	-			
Gate Resistance	R_{G}	_	1.8	3.2	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Q_g	_	15	-			
Total Gate Charge (V _{GS} = 10V)	Qg	_	33	-	nC	V _{DS} = 15V, I _D = 12A	
Gate-Source Charge	Q_{gs}	_	4.4	-	110		
Gate-Drain Charge	Q _{gd}	_	5.9	-			
Turn-On Delay Time	t _{D(on)}	_	4.4	-		$V_{DD} = 15V, V_{GS} = 10V,$ $R_L = 1.25\Omega, R_G = 3\Omega,$	
Turn-On Rise Time	tr	_	10.5	-	nS		
Turn-Off Delay Time	t _{D(off)}	_	12.3	-	113		
Turn-Off Fall Time	t _f		5.7	-			
Body Diode Reverse Recovery Time	t _{rr}		11	_	nS	104 41/44 5004/	
Body Diode Reverse Recovery Charge	Qrr	_	7.6	_	nC	I _S = 12A, dI/dt = 500A/μs	

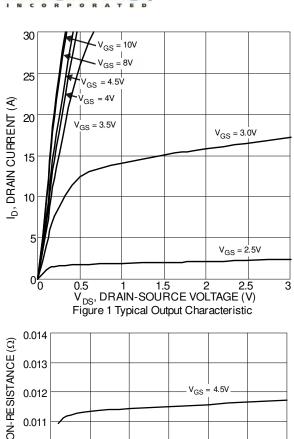
6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout. 7. Device mounted on FR-4 substrate PC board, 2oz copper, with 1-inch square copper plate. Notes:

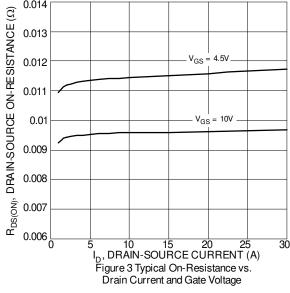
^{8.} I_{AS} and E_{AS} rating are based on low frequency and duty cycles to keep TJ = +25°C.

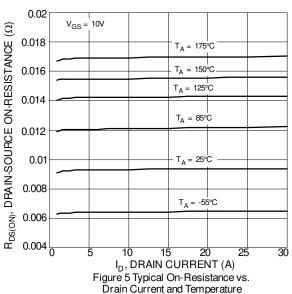
^{9.} Short duration pulse test used to minimize self-heating effect.

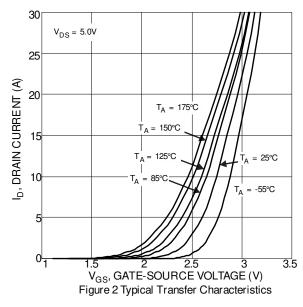
^{10.} Guaranteed by design. Not subject to product testing.

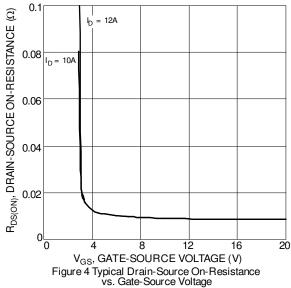


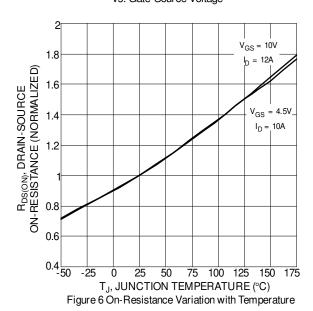




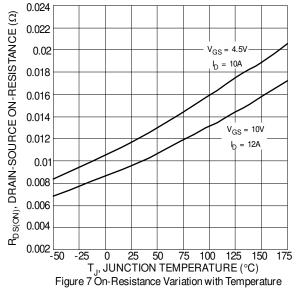


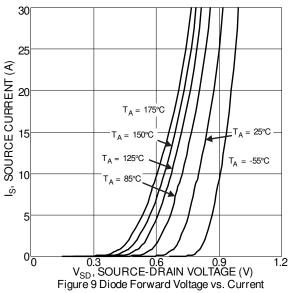


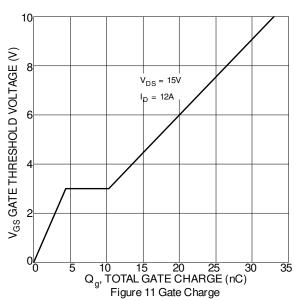












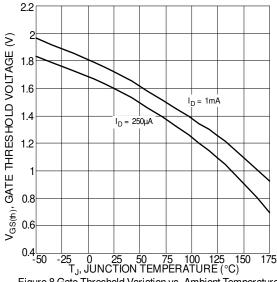
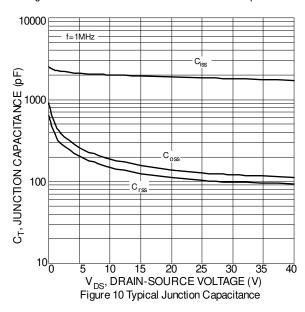
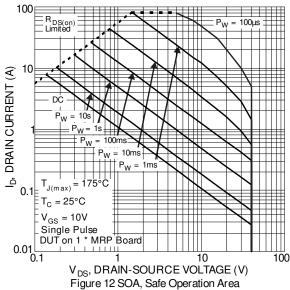
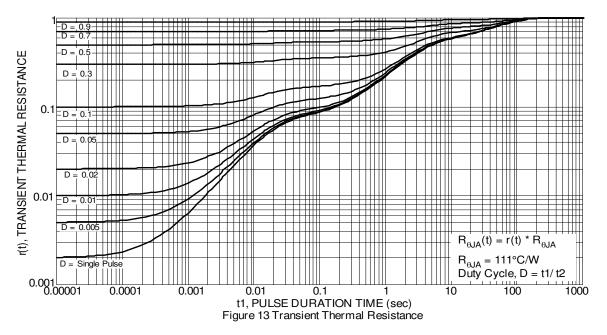


Figure 8 Gate Threshold Variation vs. Ambient Temperature





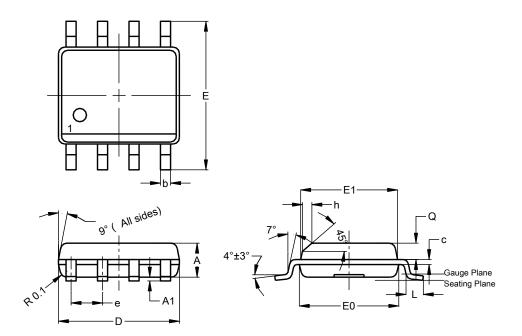




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.



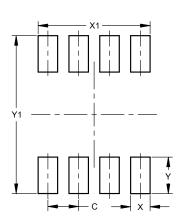


SO-8					
Dim	Min	Max	Тур		
Α	1.40	1.50	1.45		
A1	0.10	0.20	0.15		
q	0.30	0.50	0.40		
C	0.15	0.25	0.20		
D	4.85	4.95	4.90		
Е	5.90	6.10	6.00		
E1	3.80	3.90	3.85		
E0	3.85	3.95	3.90		
е	-		1.27		
h	1		0.35		
Г	0.62	0.82	0.72		
Ø	0.60	0.70	0.65		
All Dimensions in mm					



Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions Value (in mm) C 1.27 X 0.802

X1

<u>Y1</u>

4.612 1.50<u>5</u>

6.50

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SO-8

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